Joan M Redwing

List of Publications by Year
in descending order

299 papers	12,525 citations	23567 58 h-index	32842 100 g-index
306 all docs	306 docs citations	306 times ranked	11388 citing authors

#	Article	IF	Citations
1	Two-dimensional gallium nitride realized via grapheneÂencapsulation. Nature Materials, 2016, 15, 1166-1171.	27.5	626
2	In situ epitaxial MgB2 thin films for superconducting electronics. Nature Materials, 2002, 1, 35-38.	27.5	376
3	Highly Scalable, Atomically Thin WSe₂ Grown via Metalâ€“Organic Chemical Vapor Deposition. ACS Nano, 2015, 9, 2080-2087.	14.6	339
4	Bottom-up assembly of large-area nanowire resonator arrays. Nature Nanotechnology, 2008, 3, 88-92.	31.5	295
5	Crystallographic wet chemical etching of GaN. Applied Physics Letters, 1998, 73, 2654-2656.	3.3	258
6	Benchmarking monolayer MoS2 and WS2 field-effect transistors. Nature Communications, 2021, 12, 693.	12.8	246
7	High-field superconductivity in alloyedMgB2thin films. Physical Review B, 2005, 71, .	3.2	228
8	Silicon Nanowire Array Photoelectrochemical Cells. Journal of the American Chemical Society, 2007, 129, 12344-12345.	13.7	215
9	Optical properties of Si-doped GaN. Applied Physics Letters, 1997, 71, 921-923.	3.3	205
10	A roadmap for electronic grade 2D materials. 2D Materials, 2019, 6, 022001.	4.4	205
11	Diffusion-Controlled Epitaxy of Large Area Coalesced WSe₂ Monolayers on Sapphire. Nano Letters, 2018, 18, 1049-1056.	9.1	197
12	Optical Properties of Rectangular Cross-sectional ZnS Nanowires. Nano Letters, 2004, 4, 1663-1668.	9.1	194
13	An optically pumped GaNâ€“AlGaN vertical cavity surface emitting laser. Applied Physics Letters, 1996, 69, 1-3.	3.3	187
14	The role of the tunneling component in the currentâ€“voltage characteristics of metal-GaN Schottky diodes. Journal of Applied Physics, 1998, 84, 2099-2104.	2.5	177
15	Realizing Large-Scale, Electronic-Grade Two-Dimensional Semiconductors. ACS Nano, 2018, 12, 965-975.	14.6	172
16	Nanometer-Scale Modification and Welding of Silicon and Metallic Nanowires with a High-Intensity Electron Beam. Small, 2005, 1, 1221-1229.	10.0	171
17	Growth characteristics of silicon nanowires synthesized by vaporâ€“liquidâ€“solid growth in nanoporous alumina templates. Journal of Crystal Growth, 2003, 254, 14-22.	1.5	167
18	High voltage (450 V) GaN Schottky rectifiers. Applied Physics Letters, 1999, 74, 1266-1268.	3.3	149

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19	Wafer-Scale Epitaxial Growth of Unidirectional WS₂ Monolayers on Sapphire. ACS Nano, 2021, 15, 2532-2541.	14.6	149
20	Diameter Dependent Growth Rate and Interfacial Abruptness in Vaporâ€“Liquidâ€“Solid Si/Si_{1â^'x}Ge_x Heterostructure Nanowires. Nano Letters, 2008, 8, 1246-1252.	9.1	146
21	A low-power biomimetic collision detector based on an in-memory molybdenum disulfide photodetector. Nature Electronics, 2020, 3, 646-655.	26.0	140
22	Enhancement of the Superconducting Transition Temperature ofMgB2by a Strain-Induced Bond-Stretching Mode Softening. Physical Review Letters, 2004, 93, 147006.	7.8	139
23	Use of Phosphine as an n-Type Dopant Source for Vaporâ^'Liquidâ^'Solid Growth of Silicon Nanowires. Nano Letters, 2005, 5, 2139-2143.	9.1	138
24	Schottky barrier engineering in IIIâ€“V nitrides via the piezoelectric effect. Applied Physics Letters, 1998, 73, 1880-1882.	3.3	130
25	Superconducting MgB2 thin films on silicon carbide substrates by hybrid physicalâ€“chemical vapor deposition. Applied Physics Letters, 2003, 82, 2097-2099.	3.3	129
26	Measuring the specific contact resistance of contacts to semiconductor nanowires. Solid-State Electronics, 2005, 49, 227-232.	1.4	128
27	Structural and electrical properties of trimethylboron-doped silicon nanowires. Applied Physics Letters, 2004, 85, 3101-3103.	3.3	125
28	Electrochemical Investigation of the Gallium Nitrideâ€Aqueous Electrolyte Interface. Journal of the Electrochemical Society, 1995, 142, L238-L240.	2.9	110
29	Enhanced conversion efficiencies for pillar array solar cells fabricated from crystalline silicon with short minority carrier diffusion lengths. Applied Physics Letters, 2010, 96, 213503.	3.3	110
30	Capacitanceâ€“voltage characterization of AlN/GaN metalâ€“insulatorâ€“semiconductor structures grown on sapphire substrate by metalorganic chemical vapor deposition. Journal of Applied Physics, 2000, 88, 1983-1986.	2.5	108
31	Defect-Controlled Nucleation and Orientation of WSe₂ on hBN: A Route to Single-Crystal Epitaxial Monolayers. ACS Nano, 2019, 13, 3341-3352.	14.6	107
32	Vaporâ€“Liquidâ€“Solid Growth of Siliconâ€“Germanium Nanowires. Advanced Materials, 2003, 15, 2073-2076.	21.0	106
33	MgB2 thin films by hybrid physicalâ€“chemical vapor deposition. Physica C: Superconductivity and Its Applications, 2007, 456, 22-37.	1.2	105
34	Lateral Versus Vertical Growth of Two-Dimensional Layered Transition-Metal Dichalcogenides: Thermodynamic Insight into MoS₂. Nano Letters, 2016, 16, 5742-5750.	9.1	102
35	Thickness dependence of the properties of epitaxial MgB2 thin films grown by hybrid physical-chemical vapor deposition. Applied Physics Letters, 2003, 82, 4319-4321.	3.3	98
36	Lateral AlxGa1â^'xN power rectifiers with 9.7 kV reverse breakdown voltage. Applied Physics Letters, 2001, 78, 823-825.	3.3	93

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37	Properties of MgB2 thin films with carbon doping. Applied Physics Letters, 2004, 85, 2017-2019.	3.3	92
38	Ni and Ti Schottky barriers on n-AlGaN grown on SiC substrates. Applied Physics Letters, 1998, 73, 238-240.	3.3	91
39	Stranskiâ^'Krastanow Growth of Germanium on Silicon Nanowires. Nano Letters, 2005, 5, 1081-1085.	9.1	90
40	Effect of diborane on the microstructure of boron-doped silicon nanowires. Journal of Crystal Growth, 2005, 277, 428-436.	1.5	88
41	The impact of graphene properties on GaN and AlN nucleation. Surface Science, 2015, 634, 81-88.	1.9	88
42	Growth stresses and cracking in GaN films on (111) Si grown by metal-organic chemical-vapor deposition. I. AlN buffer layers. Journal of Applied Physics, 2005, 98, 023514.	2.5	87
43	Properties of Si donors and persistent photoconductivity in AlGaN. Solid-State Electronics, 1998, 42, 627-635.	1.4	84
44	Evidence of compensating centers as origin of yellow luminescence in GaN. Applied Physics Letters, 1997, 71, 3224-3226.	3.3	83
45	Radial junction silicon wire array solar cells fabricated by gold-catalyzed vapor-liquid-solid growth. Applied Physics Letters, 2010, 97, .	3.3	82
46	Diameter-Controlled Synthesis of Silicon Nanowires Using Nanoporous Alumina Membranes. Advanced Materials, 2005, 17, 114-117.	21.0	79
47	Thermally stable PtSi Schottky contact on n-GaN. Applied Physics Letters, 1997, 70, 1275-1277.	3.3	78
48	Intrinsic stresses in AlN layers grown by metal organic chemical vapor deposition on (0001) sapphire and (111) Si substrates. Journal of Applied Physics, 2004, 96, 2995-3003.	2.5	77
49	Fabrication and Characterization of Axially Doped Silicon Nanowire Tunnel Field-Effect Transistors. Nano Letters, 2010, 10, 4813-4818.	9.1	76
50	Persistent photoconductivity and defect levels in n-type AlGaN/GaN heterostructures. Applied Physics Letters, 1998, 72, 2745-2747.	3.3	75
51	Critical current density and resistivity of MgB2 films. Applied Physics Letters, 2003, 83, 102-104.	3.3	75
52	Stochastic resonance in MoS2 photodetector. Nature Communications, 2020, 11, 4406.	12.8	75
53	X-ray photoemission spectroscopic investigation of surface treatments, metal deposition, and electron accumulation on InN. Applied Physics Letters, 2003, 82, 3254-3256.	3.3	73
54	Fabrication and Electrical Properties of Si Nanowires Synthesized by Al Catalyzed Vaporâ^'Liquidâ^'Solid Growth. Nano Letters, 2009, 9, 4494-4499.	9.1	71

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55	Interfacial reactions between nickel thin films and GaN. Journal of Applied Physics, 1997, 82, 650-654.	2.5	68
56	Template-directed vaporâ€“liquidâ€“solid growth of silicon nanowires. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 389.	1.6	68
57	An Al/sub 0.3/Ga/sub 0.7/N/GaN undoped channel heterostructure field effect transistor with F/sub max/ of 107 GHz. IEEE Electron Device Letters, 1999, 20, 323-325.	3.9	63
58	Controlled synthesis of 2D transition metal dichalcogenides: from vertical to planar MoS ₂. 2D Materials, 2017, 4, 025029.	4.4	63
59	Carbon doping in metalorganic vapor phase epitaxy. Journal of Crystal Growth, 1994, 145, 382-389.	1.5	59
60	Lateral variations in threshold voltage of an AlxGa1â^'xN/GaN heterostructure field-effect transistor measured by scanning capacitance spectroscopy. Applied Physics Letters, 2001, 78, 88-90.	3.3	59
61	Growth stresses and cracking in GaN films on (111) Si grown by metalorganic chemical vapor deposition. II. Graded AlGaN buffer layers. Journal of Applied Physics, 2005, 98, 023515.	2.5	59
62	Multi-scale modeling of gas-phase reactions in metal-organic chemical vapor deposition growth of WSe2. Journal of Crystal Growth, 2019, 527, 125247.	1.5	59
63	Considerations for Utilizing Sodium Chloride in Epitaxial Molybdenum Disulfide. ACS Applied Materials & Interfaces, 2018, 10, 40831-40837.	8.0	58
64	Large Anisotropic Normal-State Magnetoresistance in CleanMgB2Thin Films. Physical Review Letters, 2006, 96, 167003.	7.8	57
65	Epitaxial Growth of Two-Dimensional Layered Transition Metal Dichalcogenides. Annual Review of Materials Research, 2020, 50, 155-177.	9.3	57
66	Diameter-Dependent Composition of Vaporâ^'Liquidâ^'Solid Grown Si₁₋_xGe_x Nanowires. Nano Letters, 2007, 7, 3241-3245.	9.1	55
67	Tin-Catalyzed Plasma-Assisted Growth of Silicon Nanowires. Journal of Physical Chemistry C, 2011, 115, 3833-3839.	3.1	54
68	Internal photoemission measurement of Schottky barrier height for Ni on AlGaN/GaN heterostructure. Applied Physics Letters, 1998, 73, 3917-3919.	3.3	51
69	Effect of damage by 2MeV He ions on the normal and superconducting properties of magnesium diboride. Applied Physics Letters, 2005, 86, 012508.	3.3	50
70	Correlation of growth stress and structural evolution during metalorganic chemical vapor deposition of GaN on (111) Si. Applied Physics Letters, 2006, 88, 041904.	3.3	50
71	Lightâ€“matter coupling in large-area van der Waals superlattices. Nature Nanotechnology, 2022, 17, 182-189.	31.5	49
72	Chalcogen Precursor Effect on Cold-Wall Gas-Source Chemical Vapor Deposition Growth of WS₂. Crystal Growth and Design, 2018, 18, 4357-4364.	3.0	48

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73	Effect of AlN interlayers on growth stress in GaN layers deposited on (111) Si. Applied Physics Letters, 2005, 87, 142101.	3.3	47
74	Influence of Carbon in Metalorganic Chemical Vapor Deposition of Few-Layer WSe2 Thin Films. Journal of Electronic Materials, 2016, 45, 6273-6279.	2.2	47
75	All-in-one, bio-inspired, and low-power crypto engines for near-sensor security based on two-dimensional memtransistors. Nature Communications, 2022, 13, .	12.8	47
76	Roomâ€Temperature Active Modulation of Valley Dynamics in a Monolayer Semiconductor through Chiral Purcell Effects. Advanced Materials, 2019, 31, e1904132.	21.0	46
77	The nature of catalyst particles and growth mechanisms of GaN nanowires grown by Ni-assisted metalâ€“organic chemical vapor deposition. Nanotechnology, 2009, 20, 085610.	2.6	45
78	Enhancement of flux pinning and high-field critical current density in carbon-alloyedMgB2thin films. Physical Review B, 2006, 74, .	3.2	44
79	Structural and electrical properties of epitaxial Bi₂Se₃ thin films grown by hybrid physical-chemical vapor deposition. Applied Physics Letters, 2012, 100, 162110.	3.3	44
80	High upper critical field and irreversibility field in MgB2 coated-conductor fibers. Applied Physics Letters, 2005, 87, 252509.	3.3	43
81	In situ stress measurements during the MOCVD growth of AlN buffer layers on (111) Si substrates. Journal of Crystal Growth, 2004, 261, 294-300.	1.5	42
82	Steady-state tensile stresses during the growth of polycrystalline films. Acta Materialia, 2007, 55, 4973-4982.	7.9	42
83	Scalable BEOL compatible 2D tungsten diselenide. 2D Materials, 2020, 7, 015029.	4.4	41
84	Effect of disorder inMgB2thin films. Physical Review B, 2005, 71, .	3.2	40
85	Tensile stress generation and dislocation reduction in Si-doped AlxGa1â^'xN films. Journal of Applied Physics, 2009, 106, .	2.5	40
86	Fundamental limitations in transferred CVD graphene caused by Cu catalyst surface morphology. Carbon, 2020, 163, 95-104.	10.3	40
87	Controllable pâ€Type Doping of 2D WSe₂ via Vanadium Substitution. Advanced Functional Materials, 2021, 31, 2105252.	14.9	40
88	Fabrication and characterisation of enhanced barrier AlGaN/GaN HFET. Electronics Letters, 1999, 35, 602.	1.0	37
89	Microwave noise performance of AlGaN/GaN HEMTs. Electronics Letters, 2000, 36, 175.	1.0	37
90	Modification of critical current density of MgB2 films irradiated with 200 MeV Ag ions. Applied Physics Letters, 2004, 84, 2352-2354.	3.3	37

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91	Dependence of penetration depth, microwave surface resistance and energy gap of MgB2 thin films on their normal-state resistivity. Superconductor Science and Technology, 2005, 18, L1-L4.	3.5	37
92	In Situ Axially Doped n-Channel Silicon Nanowire Field-Effect Transistors. Nano Letters, 2008, 8, 4359-4364.	9.1	37
93	Effect of damage by 2 MeV He ions and annealing on Hc2 in MgB2 thin films. Applied Physics Letters, 2005, 87, 072507.	3.3	36
94	Nickel and nickel silicide Schottky barrier contacts to n-type silicon nanowires. Journal of Vacuum Science & Technology B, 2008, 26, 1592.	1.3	36
95	Facet roughness analysis for InGaN/GaN lasers with cleaved facets. Applied Physics Letters, 1998, 73, 1925-1927.	3.3	35
96	Progress in the deposition of MgB2thin films. Superconductor Science and Technology, 2004, 17, S196-S201.	3.5	35
97	Effect of indium surfactant on stress relaxation by V-defect formation in GaN epilayers grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 2010, 108, .	2.5	35
98	Effect of growth conditions on the composition and structure of Si1â^'xGex nanowires grown by vaporâ€“liquidâ€“solid growth. Journal of Materials Research, 2006, 21, 2876-2881.	2.6	34
99	Temperature-Dependent Properties of Nearly Ideal ZnO Schottky Diodes. IEEE Transactions on Electron Devices, 2009, 56, 2160-2164.	3.0	34
100	Dislocation bending and tensile stress generation in GaN and AlGaN films. Journal of Crystal Growth, 2012, 359, 35-42.	1.5	34
101	Schottky Diodes on MOCVD Grown AlGaN Films.. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	33
102	SQUID magnetometer operating at 37 K based on nanobridges in epitaxial MgB2 thin films. Applied Physics Letters, 2005, 87, 192505.	3.3	33
103	Growth and Characterization of Unintentionally Doped GaSb Nanowires. Journal of Electronic Materials, 2010, 39, 355-364.	2.2	33
104	A nearâ€field scanning optical microscopy study of the photoluminescence from GaN films. Applied Physics Letters, 1996, 69, 3519-3521.	3.3	32
105	In situ stress measurements during MOCVD growth of AlGaN on SiC. Journal of Crystal Growth, 2004, 272, 65-71.	1.5	32
106	Formation of nickel germanide contacts to Ge nanowires. Applied Physics Letters, 2010, 97, 263116.	3.3	32
107	Scalable Substitutional Reâ€Doping and its Impact on the Optical and Electronic Properties of Tungsten Diselenide. Advanced Materials, 2020, 32, e2005159.	21.0	32
108	In-plane x-ray diffraction for characterization of monolayer and few-layer transition metal dichalcogenide films. Nanotechnology, 2018, 29, 055706.	2.6	30

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109	Multidimensional thermal analysis of an ultrawide bandgap AlGaN channel high electron mobility transistor. Applied Physics Letters, 2019, 115, .	3.3	30
110	Defect creation in WSe₂ with a microsecond photoluminescence lifetime by focused ion beam irradiation. Nanoscale, 2020, 12, 2047-2056.	5.6	30
111	Planar MgB2 superconductor-normal metal-superconductor Josephson junctions fabricated using epitaxial MgB2âˆ•TiB2 bilayers. Applied Physics Letters, 2006, 88, 222511.	3.3	29
112	Local electrode atom probe analysis of silicon nanowires grown with an aluminum catalyst. Nanotechnology, 2012, 23, 215205.	2.6	29
113	Metalorganic chemical vapor deposition of N-polar GaN films on vicinal SiC substrates using indium surfactants. Applied Physics Letters, 2012, 100, .	3.3	29
114	Effect of AlN buffer layers on the surface morphology and structural properties of N-polar GaN films grown on vicinal C-face SiC substrates. Journal of Crystal Growth, 2013, 377, 51-58.	1.5	29
115	Scalable low-temperature synthesis of two-dimensional materials beyond graphene. JPhys Materials, 2020, 4, 012001.	4.2	29
116	Oxidation of silicon nanowires for top-gated field effect transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 370-374.	2.1	28
117	Substrate effects on GaN photoconductive detector performance. Applied Physics Letters, 1999, 75, 25-27.	3.3	27
118	Suppression of the vaporâ€“liquidâ€“solid growth of silicon nanowires by antimony addition. Nanotechnology, 2009, 20, 025607.	2.6	27
119	High-Jcâ€ˆMgB2 Josephson junctions with operating temperature up to 40 K. Applied Physics Letters, 2010, 96, .	3.3	27
120	In situ growth of MgB/sub 2/ thin films by hybrid physical-chemical vapor deposition. IEEE Transactions on Applied Superconductivity, 2003, 13, 3233-3237.	1.7	26
121	Resistivity measurements of intentionally and unintentionally template-grown doped silicon nanowire arrays. Nanotechnology, 2007, 18, 315201.	2.6	26
122	Evolution of threading dislocations in MOCVD-grown GaN films on (111) Si substrates. Journal of Crystal Growth, 2007, 300, 217-222.	1.5	26
123	Thin Film Transistors Using Wafer-Scale Low-Temperature MOCVD WSe2. Journal of Electronic Materials, 2016, 45, 6280-6284.	2.2	26
124	Understanding Interlayer Coupling in TMD-hBN Heterostructure by Raman Spectroscopy. IEEE Transactions on Electron Devices, 2018, 65, 4059-4067.	3.0	26
125	Hexagonal Boron Nitride Crystal Growth from Iron, a Single Component Flux. ACS Nano, 2021, 15, 7032-7039.	14.6	26
126	Illuminating Invisible Grain Boundaries in Coalesced Single-Orientation WS₂ Monolayer Films. Nano Letters, 2021, 21, 6487-6495.	9.1	26

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127	Monolayer MoS₂ on sapphire: an azimuthal reflection high-energy electron diffraction perspective. 2D Materials, 2021, 8, 025003.	4.4	26
128	Scanning capacitance microscopy of AlGaN/GaN heterostructure field-effect transistor epitaxial layer structures. Applied Physics Letters, 1999, 75, 2250-2252.	3.3	25
129	Vibrational and optical properties of GaN nanowires synthesized by Ni-assisted catalytic growth. Nanotechnology, 2007, 18, 445704.	2.6	25
130	Fabrication of Cobalt Silicide Nanowire Contacts to Silicon Nanowires. Journal of the Electrochemical Society, 2003, 150, G577.	2.9	24
131	Electron scattering dependence of dendritic magnetic instability in superconducting MgB2 films. Applied Physics Letters, 2004, 85, 5284-5286.	3.3	24
132	Upper Critical Fields Up to 60 T in Dirty Magnesium Diboride Thin Films. IEEE Transactions on Applied Superconductivity, 2005, 15, 3234-3237.	1.7	24
133	Growth of thick p-type SiC epitaxial layers by halide chemical vapor deposition. Journal of Crystal Growth, 2008, 310, 4088-4093.	1.5	24
134	Raman Scattering from Si₁₋_xGe_x Alloy Nanowires. Journal of Physical Chemistry C, 2008, 112, 3209-3215.	3.1	24
135	Epitaxial growth of few-layer Î²-In2Se3 thin films by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2020, 533, 125471.	1.5	24
136	Scanning electron microscope studies of AlGaN films grown by organometallic vapor phase epitaxy. Solid-State Electronics, 1998, 42, 637-646.	1.4	23
137	In situ measurement of stress generation arising from dislocation inclination in AlxGa1âˆ’xN:Si thin films. Applied Physics Letters, 2008, 93, 111910.	3.3	23
138	Surface morphology and thickness dependence of the properties of MgB₂thin films by hybrid physicalâ€“chemical vapor deposition. Superconductor Science and Technology, 2010, 23, 055004.	3.5	23
139	Ultrafast Electrical Measurements of Isolated Silicon Nanowires and Nanocrystals. Journal of Physical Chemistry Letters, 2014, 5, 2050-2057.	4.6	23
140	Atomic layer deposition of ZnO on MoS2 and WSe2. Applied Surface Science, 2019, 480, 43-51.	6.1	23
141	In situ observation of coalescence-related tensile stresses during metalorganic chemical vapor deposition of GaN on sapphire. Applied Physics Letters, 2005, 86, 261907.	3.3	22
142	FDTD modeling of solar energy absorption in silicon branched nanowires. Optics Express, 2013, 21, A392.	3.4	22
143	Photoelastic waveguides and the controlled introduction of strain in IIIâ€V semiconductors by means of thin film technology. Journal of Applied Physics, 1995, 78, 236-244.	2.5	21
144	Current limitation after pinch-off in AlGaN/GaN FETs. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 1.	1.0	21

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145	Effect of polarity on the growth of InN films by metalorganic chemical vapor deposition. Journal of Applied Physics, 2008, 104, .	2.5	21
146	High-field properties of carbon-doped MgB₂thin films by hybrid physicalâ€“chemical vapor deposition using different carbon sources. Superconductor Science and Technology, 2011, 24, 125014.	3.5	21
147	Hexagonal Boron Nitride Single Crystal Growth from Solution with a Temperature Gradient. Chemistry of Materials, 2020, 32, 5066-5072.	6.7	21
148	High-Density, Localized Quantum Emitters in Strained 2D Semiconductors. ACS Nano, 2022, 16, 9651-9659.	14.6	21
149	Characterisation of rhenium Schottky contacts on n-type AlxGa1â€“xN. Electronics Letters, 1999, 35, 745.	1.0	20
150	Terahertz surface impedance of epitaxial MgB2 thin film. Applied Physics Letters, 2005, 87, 092503.	3.3	20
151	Nanoscale disorder in high critical field, carbon-doped MgB2 hybrid physical-chemical vapor deposition thin films. Applied Physics Letters, 2007, 91, 082513.	3.3	20
152	Effect of reactor pressure on catalyst composition and growth of GaSb nanowires. Journal of Crystal Growth, 2010, 312, 514-519.	1.5	20
153	Modeling for Structural Engineering and Synthesis of Two-Dimensional WSe₂ Using a Newly Developed ReaxFF Reactive Force Field. Journal of Physical Chemistry C, 2020, 124, 28285-28297.	3.1	20
154	Degradation of<tex>$rm MgB_2$</tex>Thin Films in Water. IEEE Transactions on Applied Superconductivity, 2005, 15, 224-227.	1.7	19
155	Evolution of Threading Dislocation Density and Stress in GaN Films Grown on (111) Si Substrates by Metalorganic Chemical Vapor Deposition. Journal of Electronic Materials, 2007, 36, 346-352.	2.2	19
156	Effect of substrate on the growth and properties of thin 3R NbS2 films grown by chemical vapor deposition. Journal of Crystal Growth, 2018, 486, 137-141.	1.5	19
157	Photoluminescence studies of erbium-doped GaAs under hydrostatic pressure. Journal of Applied Physics, 1997, 82, 368-374.	2.5	18
158	Modeling studies of the chemical vapor deposition of boron films from B2H6. Journal of Crystal Growth, 2007, 299, 358-364.	1.5	18
159	Growth of Thick MgB₂ Films by Impingingâ€Jet Hybrid Physicalâ€Chemical Vapor Deposition. Advanced Materials, 2008, 20, 319-323.	21.0	18
160	Locally defined quantum emission from epitaxial few-layer tungsten diselenide. Applied Physics Letters, 2019, 114, .	3.3	18
161	Interface Transparency and Rashba Spin Torque Enhancement in WSe2 Heterostructures. ACS Applied Materials & Interfaces, 2021, 13, 13744-13750.	8.0	18
162	Growth studies of erbiumâ€doped GaAs deposited by metalorganic vapor phase epitaxy using novel cyclopentadienylâ€based erbium sources. Journal of Applied Physics, 1994, 76, 1585-1591.	2.5	17

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163	Evolution of surface morphology and film stress during MOCVD growth of InN on sapphire substrates. Journal of Crystal Growth, 2004, 269, 128-133.	1.5	17
164	Raman scattering in pure and carbon-dopedMgB2films. Physical Review B, 2005, 71, .	3.2	17
165	Single wire radial junction photovoltaic devices fabricated using aluminum catalyzed silicon nanowires. Nanotechnology, 2011, 22, 445401.	2.6	17
166	Crystallographic Wet Chemical Etching of p-Type GaN. Journal of the Electrochemical Society, 2000, 147, 763.	2.9	16
167	Thermodynamic equilibrium limitations on the growth of SiC by halide chemical vapor deposition. Journal of Applied Physics, 2007, 101, 014903.	2.5	16
168	The effect of polarity on MOCVD growth of thick InGaN. Applied Physics Letters, 2017, 110, .	3.3	16
169	Sulfidation of 2D transition metals (Mo, W, Re, Nb, Ta): thermodynamics, processing, and characterization. Journal of Materials Science, 2017, 52, 10127-10139.	3.7	16
170	Multi-wafer batch synthesis of graphene on Cu films by quasi-static flow chemical vapor deposition. 2D Materials, 2019, 6, 045032.	4.4	16
171	Study of the gas phase chemistry in the silicon doping of GaAs grown by metalorganic vapor phase epitaxy using tertiarybutylarsine as the group V source. Journal of Crystal Growth, 1994, 135, 423-433.	1.5	15
172	Gate recessing of GaN MESFETs using photoelectrochemical wet etching. Electronics Letters, 1999, 35, 2140.	1.0	15
173	AlGaN/GaN MODFETs on semi-insulating SiC with 3 W/mm at 20 GHz. Electronics Letters, 2000, 36, 1234.	1.0	15
174	Aluminum-catalyzed silicon nanowires: Growth methods, properties, and applications. Applied Physics Reviews, 2016, 3, .	11.3	15
175	Interdependence of Electronic and Thermal Transport in Al_xGa_{1â€“x}N Channel HEMTs. IEEE Electron Device Letters, 2020, 41, 461-464.	3.9	15
176	Substrate Modification during Chemical Vapor Deposition of hBN on Sapphire. ACS Applied Materials & Interfaces, 2021, 13, 54516-54526.	8.0	15
177	Spin-dependent vibronic response of a carbon radical ion in two-dimensional WS2. Nature Communications, 2021, 12, 7287.	12.8	15
178	Clean epitaxial MgB₂films fabricated by theex situannealing of chemical vapour deposition-grown B films in Mg vapour. Superconductor Science and Technology, 2008, 21, 045005.	3.5	14
179	A simple reflectance method for estimation of the Al mole fraction of bulk AlGaN and AlGaN/GaN heterostructures. Applied Physics Letters, 1999, 75, 1419-1421.	3.3	13
180	Growth and process modeling studies of nickel-catalyzed metalorganic chemical vapor deposition of GaN nanowires. Journal of Crystal Growth, 2009, 311, 3409-3416.	1.5	13

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